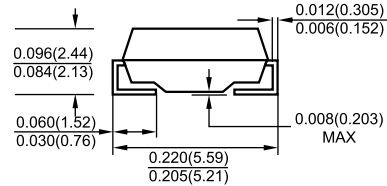
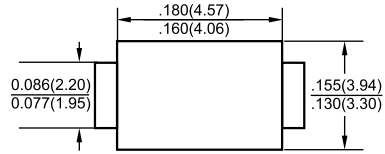




### SMB/DO-214AA

## Features

- ✧ For surface mounted application
- ✧ Glass passivated junction chip.
- ✧ Low forward voltage drop
- ✧ High current capability
- ✧ Easy pick and place
- ✧ High surge current capability
- ✧ Plastic material used carries Underwriters Laboratory Classification 94V-0
- ✧ High temperature soldering: 260°C / 10 seconds at terminals



## Mechanical Data

Dimensions in inches and (millimeters)

- ✧ Case: Molded plastic
- ✧ Terminals: Pure tin plated, lead free.
- ✧ Polarity: Indicated by cathode band
- ✧ Weight: 0.093 gram

## Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	S3AB	S3BB	S3DB	S3GB	S3JB	S3KB	S3MB	Units
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @ $T_L = 75^\circ\text{C}$	$I_{(AV)}$	3.0							A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	$I_{FSM}$	80							A
Maximum Instantaneous Forward Voltage @ 3.0A	$V_F$	1.15							V
Maximum DC Reverse Current @ $T_A = 25^\circ\text{C}$ at Rated DC Blocking Voltage @ $T_A = 125^\circ\text{C}$	$I_R$	10 250							 uA
Typical Reverse Recovery Time ( Note 1 )	$T_{rr}$	1.5							uS
Typical Junction Capacitance ( Note 2 )	$C_j$	40							pF
Typical Thermal Resistance (Note 3)	$R_{\theta JL}$	10							°C/W
Operating Temperature Range	$T_J$	-55 to +150							°C
Storage Temperature Range	$T_{STG}$	-55 to +150							°C

- Notes:
1. Reverse Recovery Test Conditions:  $I_F = 0.5\text{A}$ ,  $I_R = 1.0\text{A}$ ,  $I_{RR} = 0.25\text{A}$
  2. Measured at 1 MHz and Applied  $V_R = 4.0$  Volts
  3. Measured on P.C. Board with 0.4" x 0.4" (10mm x 10mm) Copper Pad Areas.

### RATINGS AND CHARACTERISTIC CURVES (S3AB THRU S3MB)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

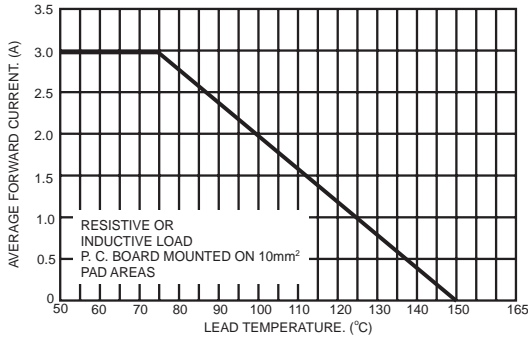


FIG.2- TYPICAL REVERSE CHARACTERISTICS

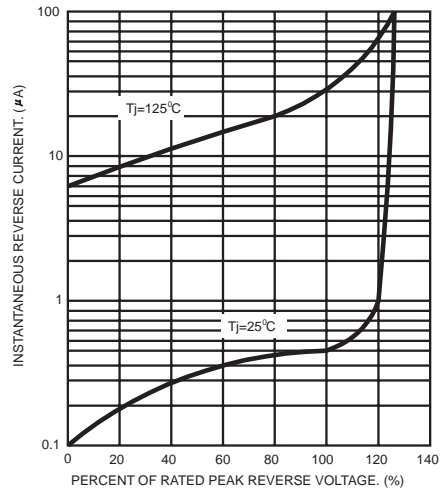


FIG.3- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

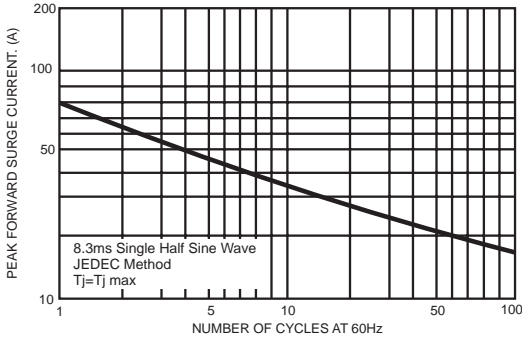


FIG.5- TYPICAL FORWARD CHARACTERISTICS

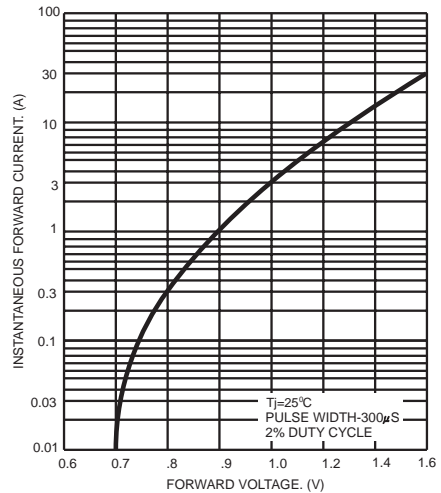


FIG.4- TYPICAL JUNCTION CAPACITANCE

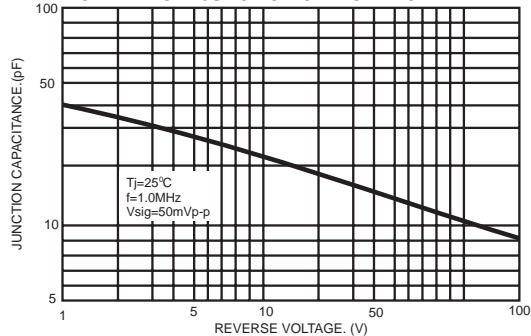
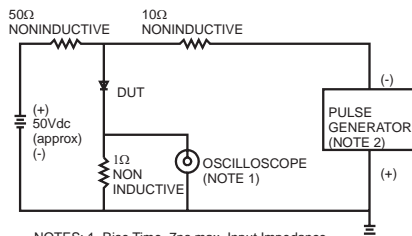


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



NOTES: 1. Rise Time=7ns max. Input Impedance=1 megohm 22pf  
2. Rise Time=10ns max. Source Impedance=50 ohms

